1. Record Nr. UNISA990000247620203316

Autore	HALL, Marty
Titolo	Core : web programming / Marty Hall
Pubbl/distr/stampa	Upper Saddle River : Prentice-Hall, copyr. 1998
ISBN	0-13-625666-X
Descrizione fisica	XL, 1277 p. : ill. ; 24 cm. + CD-Rom
Disciplina	005.2
Soggetti	Elaboratori elettronici - Programmazione Internet <reti di elaboratori> World Wide Web <sistema di recupero delle informazioni>
Collocazione	005.2 HAL
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia

2. Record Nr. UNINA9910454981803321

Titolo	Topics in Fluorescence Spectroscopy : Principles [[electronic resource] /] / edited by Joseph R. Lakowicz
Pubbl/distr/stampa	New York, : Kluwer Academic, c2002
ISBN	1-280-20633-0 9786610206339 0-306-47058-6
Edizione	[1st ed. 2002.]
Descrizione fisica	1 online resource (449 p.)
Collana	Topics in fluorescence spectroscopy ; ; v.2
Altri autori (Persone)	LakowiczJoseph R
Disciplina	543/.0858
Soggetti	Diagnostic imaging Fluorescence spectroscopy Lasers - Diagnostic use Electronic books.
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Note generali	Description based upon print version of record.
Nota di bibliografia	Includes bibliographical references and index.
Nota di contenuto	Fluorescence Anisotropy: Theory and Applications -- Fluorescence Quenching: Theory and Applications -- Resonance Energy Transfer -- Least-Squares Analysis of Fluorescence Data -- The Global Analysis of Fluorescence Intensity and Anisotropy Decay Data: Second-Generation Theory and Programs -- Fluorescence Polarization from Oriented Systems -- Fluorescence-Based Fiber-Optic Sensors -- Inhomogeneous Broadening of Electronic Spectra of Dye Molecules in Solutions.
Sommario/riassunto	Fluorescence spectroscopy and its applications to the physical and life sciences have evolved rapidly during the past decade. The increased interest in fluorescence appears to be due to advances in time resolution, methods of data analysis, and improved instrumentation. With these advances, it is now practical to perform time-resolved measurements with enough resolution to compare the results with the structural and dynamic features of mac- molecules, to probe the structures of proteins, membranes, and nucleic acids, and to acquire two-dimensional microscopic images of chemical or protein distributions in cell cultures. Advances in laser and detector technology have also resulted in renewed interest in fluorescence for clinical and

	analytical chemistry. Because of these numerous developments and the rapid appearance of new methods, it has become difficult to remain current on the science of fluorescence and its many applications. Consequently, I have asked the experts in particular areas of fluorescence to summarize their knowledge and the current state of the art. This has resulted in the initial two volumes of Topics in Fluorescence Spectroscopy, which is intended to be an ongoing series which summarizes, in one location, the vast literature on fluorescence spectroscopy. The third volume will appear shortly. The first three volumes are designed to serve as an advanced text. These volumes describe the more recent techniques and technologies (Volume 1), the principles governing fluorescence and the experimental observables (Volume 2), and applications in biochemistry and biophysics (Volume 3).

3.

Record Nr.	UNINA9910831054003321
Autore	Bahl I. J
Titolo	Fundamentals of RF and microwave transistor amplifiers [[electronic resource] /] / Inder Bahl
Pubbl/distr/stampa	Oxford, : Wiley, 2009
ISBN	1-282-36840-0 9786612368400 0-470-46234-5 0-470-46231-0
Descrizione fisica	1 online resource (697 p.)
Disciplina	621.3815/35 621.381535
Soggetti	Amplifiers, Radio frequency Microwave amplifiers Transistor amplifiers
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Note generali	Description based upon print version of record.
Nota di bibliografia	Includes bibliographical references and index.
Nota di contenuto	Fundamentals of RF and Microwave Transistor Amplifiers; Contents in

Brief; Contents; Foreword; Preface; 1. Introduction; 1.1. Transistor Amplifier; 1.2. Early History of Transistor Amplifiers; 1.3. Benefits of Transistor Amplifiers; 1.4. Transistors; 1.5. Design of Amplifiers; 1.6. Amplifier Manufacturing Technologies; 1.7. Applications of Amplifiers; 1.8. Amplifier Cost; 1.9. Current Trends; 1.10. Book Organization; References; 2. Linear Network Analysis; 2.1. Impedance Matrix; 2.2. Admittance Matrix; 2.3. ABCD Parameters; 2.4. S-Parameters; 2.4.1. S-Parameters for a One-Port Network
2.5. Relationships Between Various Two-Port ParametersReferences; Problems; 3. Amplifier Characteristics and Definitions; 3.1. Bandwidth; 3.2. Power Gain; 3.3. Input and Output VSWR; 3.4. Output Power; 3.5. Power Added Efficiency; 3.6. Intermodulation Distortion; 3.6.1. IP3; 3.6.2. ACPR; 3.6.3. EVM; 3.7. Harmonic Power; 3.8. Peak-to-Average Ratio; 3.9. Combiner Efficiency; 3.10. Noise Characterization; 3.10.1. Noise Figure; 3.10.2. Noise Temperature; 3.10.3. Noise Bandwidth; 3.10.4. Optimum Noise Match; 3.10.5. Constant Noise Figure and Gain Circles; 3.10.6. Simultaneous Input and Noise Match
3.11. Dynamic Range3.12. Multistage Amplifier Characteristics; 3.12.1. Multistage IP3; 3.12.2. Multistage PAE; 3.12.3. Multistage NF; 3.13. Gate and Drain Pushing Factors; 3.14. Amplifier Temperature Coefficient; 3.15. Mean Time to Failure; References; Problems; 4. Transistors; 4.1. Transistor Types; 4.2. Silicon Bipolar Transistor; 4.2.1. Figure of Merit; 4.2.2. High-Frequency Noise Performance of Silicon BJT; 4.2.3. Power Performance; 4.3. GaAs MESFET; 4.3.1. Small-Signal Equivalent Circuit; 4.3.2. Figure of Merit; 4.3.3. High-Frequency Noise Properties of MESFETs
4.4. Heterojunction Field Effect Transistor4.4.1. High-Frequency Noise Properties of HEMTs; 4.4.2. Indium Phosphide pHEMTs; 4.5. Heterojunction Bipolar Transistors; 4.5.1. High-Frequency Noise Properties of HBTs; 4.5.2. SiGe Heterojunction Bipolar Transistors; 4.6. MOSFET; References; Problems; 5. Transistor Models; 5.1. Transistor Model Types; 5.1.1. Physics/Electromagnetic Theory Based Models; 5.1.2. Analytical or Hybrid Models; 5.1.3. Measurement Based Models; 5.2. MESFET Models; 5.2.1. Linear Models; 5.2.2. Nonlinear Models; 5.3. pHEMT Models; 5.3.1. Linear Models; 5.3.2. Nonlinear Models
5.4. HBT Model5.5. MOSFET Models; 5.6. BJT Models; 5.7. Transistor Model Scaling; 5.8. Source-Pull and Load-Pull Data; 5.8.1. Theoretical Load-Pull Data; 5.8.2. Measured Power and PAE Source Pull and Load Pull; 5.8.3. Measured IP3 Source and Load Impedance; 5.8.4. Source and Load Impedance Scaling; 5.9. Temperature-Dependent Models; References; Problems; 6. Matching Network Components; 6.1. Impedance Matching Elements; 6.2. Transmission Line Matching Elements; 6.2.1. Microstrip; 6.2.2. Coplanar Lines; 6.3. Lumped Elements; 6.3.1. Capacitors; 6.3.2. Inductors; 6.3.3. Resistors
6.4. Bond Wire Inductors

Sommario/riassunto

A Comprehensive and Up-to-Date Treatment of RF and Microwave Transistor Amplifiers This book provides state-of-the-art coverage of RF and microwave transistor amplifiers, including low-noise, narrowband, broadband, linear, high-power, high-efficiency, and high-voltage. Topics covered include modeling, analysis, design, packaging, and thermal and fabrication considerations. Through a unique integration of theory and practice, readers will learn to solve amplifier-related design problems ranging from matching networks to biasing and stability. More than 240 problems are included to help read